

PNP Low Saturation Transistor

These devices are designed for high current gain and low saturation voltage with collector currents up to 2.0 A continuous. Sourced from Process PB.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units | |
|-----------------------------------|--|-------------|-------|--|
| V _{CEO} | Collector-Emitter Voltage | 30 | V | |
| V _{CBO} | Collector-Base Voltage | 35 | V | |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V | |
| lc | Collector Current - Continuous | 2.0 | А | |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C | |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Max | Units | |
|------------------|---|------------------|-------|--|
| | | FPN430 / FPN430A | | |
| PD | Total Device Dissipation | 1.0 | W | |
| R _{θJC} | Thermal Resistance, Junction to Case | 50 | °C/W | |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | 125 | °C/W | |

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PNP Low Saturation Transistor

(continued)

| Symbol | Parameter | Test Conditions | Min | Max | Units |
|-------------------|--|---|-----|-----------|----------|
| | | | | | |
| OFF CHA | RACTERISTICS | | | | |
| BV _{CEO} | Collector-Emitter Breakdown Voltage | $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$ | 30 | | V |
| BV _{CBO} | Collector-Base Breakdown Voltage | $I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$ | 35 | | V |
| BV _{EBO} | Emitter-Base Breakdown Voltage | $I_{\rm E} = 100 \ \mu {\rm A}, \ I_{\rm C} = 0$ | 5.0 | | V |
| I _{CBO} | Collector Cutoff Current | $V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = 100^{\circ}\text{C}$ | | 100 10 | nA μA |
| I _{EBO} | Emitter Cutoff Current | $V_{EB} = 4.0 \text{ V}, I_{C} = 0$ | | 100 | nA |

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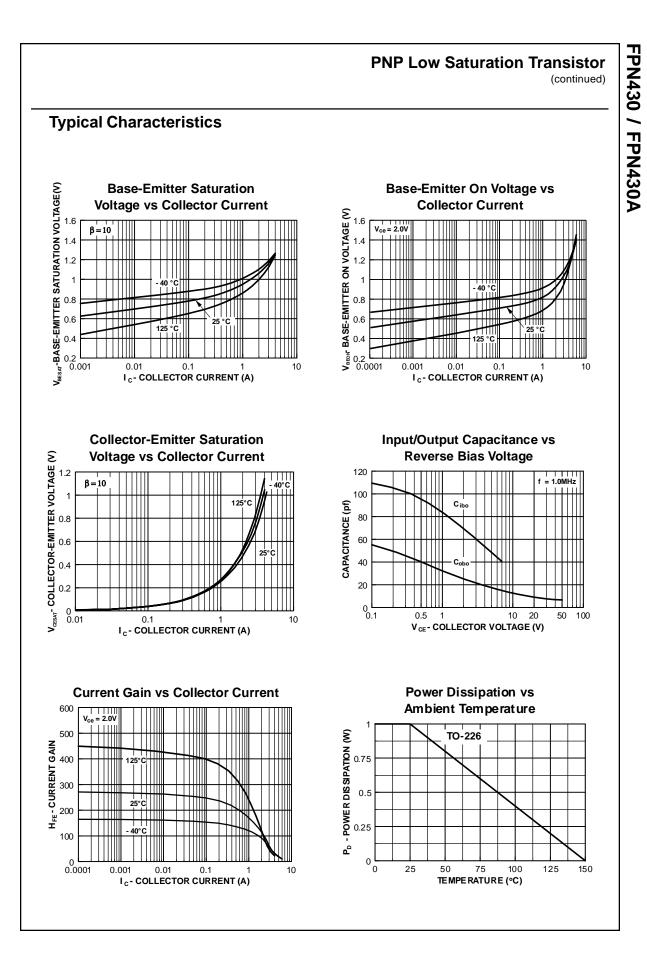
| h _{FE} | DC Current Gain | $I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 2.0 \text{ V}$ | 430 | 100 | | |
|----------------------|--------------------------------------|--|------|-----|------|----|
| | | | 430A | 250 | | |
| | | $I_{C} = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$ | | 60 | | |
| | | $I_{C} = 2.0 \text{ A}, V_{CE} = 2.0 \text{ V}$ | | 40 | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_{\rm C} = 1.0 \text{ A}, I_{\rm B} = 100 \text{ mA}$ | 430 | | 500 | mV |
| . , | | | 430A | | 450 | mV |
| | | $I_{\rm C} = 2.0 \text{ A}, I_{\rm B} = 200 \text{ mA}$ | | | 800 | mV |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | $I_{\rm C}$ = 1.0 A, $I_{\rm B}$ = 100 mA | | | 1.25 | V |
| V _{BE(on)} | Base-Emitter Saturation Voltage | $I_{C} = 1.0 \text{ A}, V_{CE} = 2.0 \text{ V}$ | | | 1.0 | V |

SMALL SIGNAL CHARACTERISTICS

| Cobo | Output Capacitance | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ | | 25 | pF |
|------|----------------------|---|-----|----|-----|
| FT | Transition Frequency | I_{C} = 100 mA, V_{CE} = 5.0 V, f = 100 MHz | 100 | | MHz |

*Pulse Test: Pulse Width ${\leq}\,300\,\mu\text{s},$ Duty Cycle ${\leq}\,2.0\%$

NOTE: All voltages (V) and currents (A) are negative polarity for PNP transistors.



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|--------------------------|---------------------------|---|
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